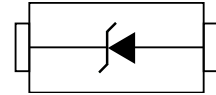


The PESDNC5D3V3U protects sensitive semiconductor components from damage or upset due to electrostatic discharge (ESD) and other voltage induced transient events. They feature large cross-sectional area junctions for conducting high transient currents, offer desirable electrical characteristics for board level protection, such as fast response time, low operating voltage. It gives designer the flexibility to protect one unidirectional line in applications where arrays are not practical.



Feature

- 150W peak pulse power per line ($t_P = 8/20\mu s$)
- SOD-523 package
- Replacement for MLV(0603)
- Unidirectional configurations
- Response time is typically $< 1\text{ ns}$
- Protect one I/O or power line
- Low clamping voltage
- RoHS compliant
- Transient protection for data lines to IEC 61000-4-2(ESD) $\pm 30\text{KV}$ (air), $\pm 30\text{KV}$ (contact); IEC 61000-4-4 (EFT) 40A (5/50ns)

Applications

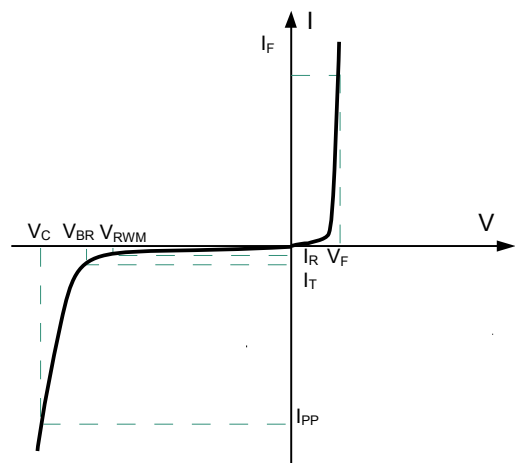
- Cellular phones
- Portable devices
- Digital cameras
- Power supplies

Mechanical Characteristics

- Lead finish:100% matte Sn(Tin) Mounting
- position: Any
- Qualified max reflow temperature:260°C
- Device meets MSL 1 requirements
- Pure tin plating: 7 ~ 17 μm
- Pin flatness: $\leq 3\text{mil}$

Electronics Parameter

Symbol	Parameter
V_{RWM}	Peak Reverse Working Voltage
I_R	Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
P_{PP}	Peak Pulse Power
C_J	Junction Capacitance
I_F	Forward Current
V_F	Forward Voltage @ I_F



Electrical characteristics per line@25°C (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
Reverse Stand-off Voltage	V_{RWM}				3.3	V
Reverse Breakdown Voltage	V_{BR}	$I_t = 1mA$	5			V
Reverse Leakage Current	I_R	$RWM = 3.3V \quad T=25^\circ C$			1	μA
Clamping Voltage	V_C	$I_{PP} = 1A \quad t_p = 8/20\mu s$			5.8	V
Clamping Voltage	V_C	$I_{PP} = 5A \quad t_p = 8/20\mu s$			8.8	V
Junction Capacitance	C_j	$V_R=0V \quad f = 1MHz$		120		pF

Absolute maximum rating@25°C

Rating	Symbol	Value	Units
Unidirectional Peak Pulse Power ($t_p=8/20\mu S$)	P_{pp}	150	W
Operating Temperature	T_J	-55 to +150	$^\circ C$
Storage Temperature	T_{STG}	-55 to +150	$^\circ C$

Typical Characteristics

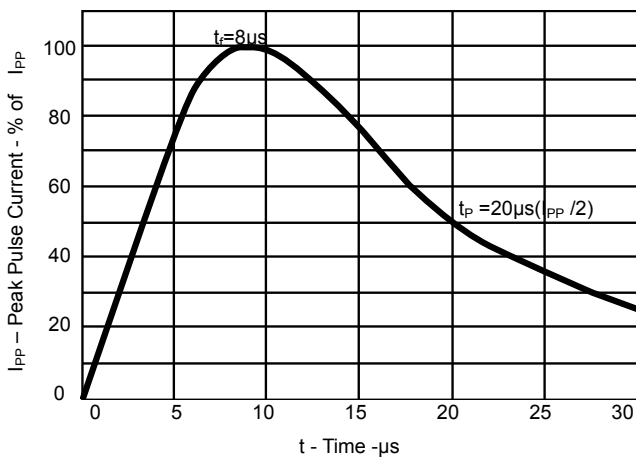


Fig 1.Pulse waveform

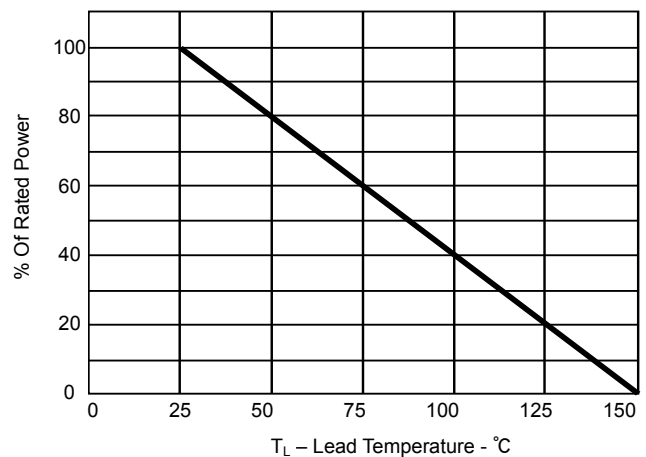


Fig 2.Power derating curve

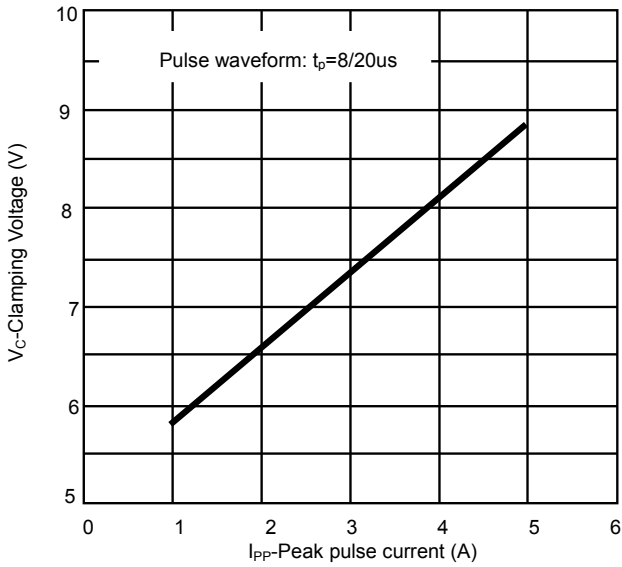


Fig 3. Clamping voltage vs. Peak pulse current

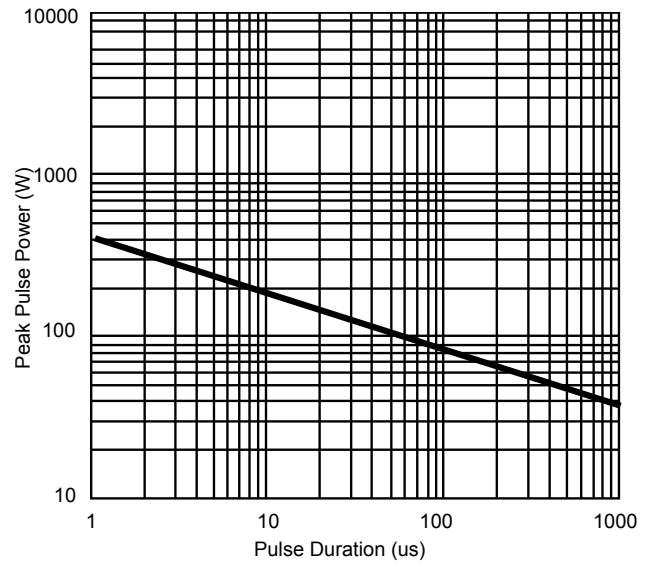
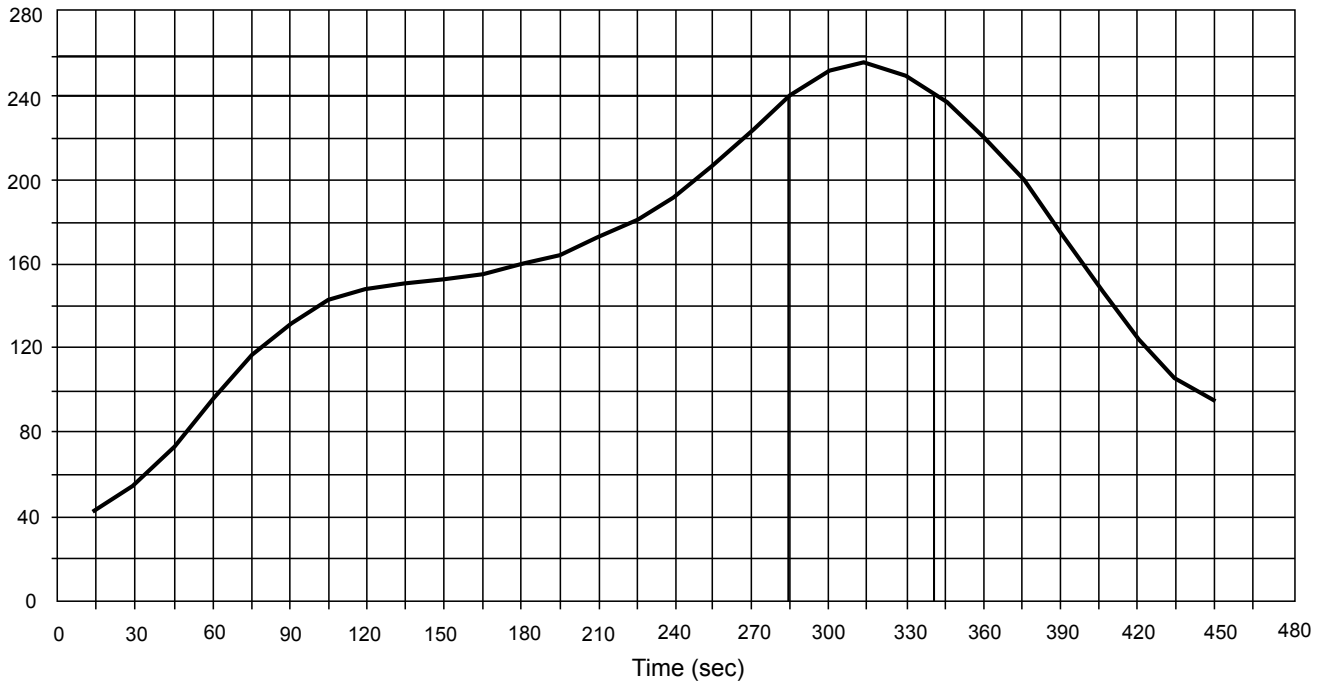


Fig 4. Non repetitive peak pulse power vs. Pulse time

Solder Reflow Recommendation

Peak Temp=257°C, Ramp Rate=0.802deg. °C/sec



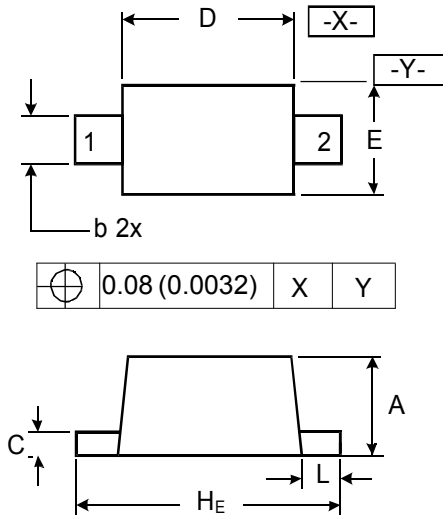
PCB Design

For TVS diodes a low-ohmic and low-inductive path to chassis earth is absolutely mandatory in order to achieve good ESD protection. Novices in the area of ESD protection should take following suggestions to heart:

- Do not use stubs, but place the cathode of the TVS diode directly on the signal trace.
- Do not make false economies and save copper for the ground connection.
- Place via holes to ground as close as possible to the anode of the TVS diode.
- Use as many via holes as possible for the ground connection.
- Keep the length of via holes in mind! The longer the more inductance they will have.

Package outline dimensions

SOD-523



DIMENSIONS

SYMBOL	MILLIMETER		INCHES	
	MIN	MAX	MIN	MAX
A	0.50	0.70	0.020	0.028
b	0.25	0.35	0.010	0.014
C	0.07	0.20	0.0028	0.0079
D	1.10	1.30	0.043	0.051
E	0.70	0.90	0.028	0.035
H _E	1.50	1.70	0.059	0.067
L	0.15	0.25	0.006	0.010

Marking



Ordering information

Order code	Package	Base qty	Delivery mode
UMW PESDNC5D3V3U	SOD-523	3000	Tape and reel

单击下面可查看定价，库存，交付和生命周期等信息

[>>UMW\(友台半导体\)](#)